

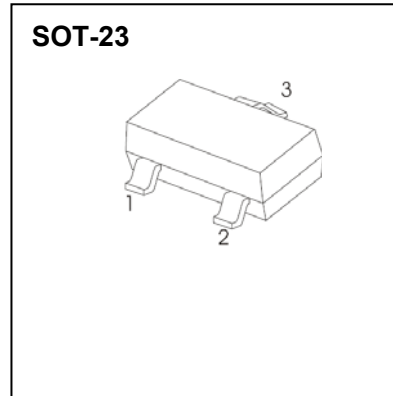


DONGGUAN NANJING ELECTRONICS LTD.,
SOT-23 Plastic-Encapsulate Diodes

BAV23A/C/S SCHOTTKY BARRIER DIODE

FEATURES

- Fast Switching Speed
- High Conductance
- For General Purpose Switching Applications



BAV23A	BAV23C	BAV23S
MARKING: KT7	MARKING: KT6	MARKING: KL31

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	250	V
V _{RWM}	Working Peak Reverse Voltage		
V _{R(RMS)}	RMS Reverse Voltage	175	V
I _O	Average Rectified Output Current	400	mA
I _{FSM}	Non-repetitive Peak Forward Surge Current @ t=1μs	9	A
	@ t=100μs	3	A
	@ t=10ms	1.7	A
P _D	Power Dissipation	350	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	286	°C/W
T _j	Junction Temperature	125	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V _(BR)	I _R =100μA	250			V
Reverse current	I _R	V _R =250V			0.1	μA
Forward voltage	V _F	I _F =100mA			1	V
		I _F =200mA			1.25	
Total capacitance	C _{tot}	V _R =0V, f=1MHz			5	pF
Reverse recovery time	t _{rr}	I _F = I _R =30mA, I _{rr} =0.1×I _R , R _L =100Ω			50	ns